

14. (ONCE AMENDED) A semiconductor device comprising:

a first insulating layer;

a first conductive layer having wiring patterns and formed within the first insulating layer;

a second conductive layer having wiring patterns and formed over the first insulating layer, one or more of the wiring patterns of the second conductive layer being electrically connected to one or more of the wiring patterns of the first conductive layer through via holes; and

at least one semiconductor element imbedded within the first insulating layer such that the at least one semiconductor element is electrically connected to at least one of the wiring patterns of the first conductive layer and at least one of the wiring patterns of the second conductive layer.

15. (ONCE AMENDED) The semiconductor device according to claim 14, further comprising a second insulating layer having at least one semiconductor element imbedded therein, the second insulating layer provided on the first insulating layer and containing therein the second conductive layer, and the at least one semiconductor element of the second insulating layer being electrically connected to one or more of the wiring patterns of the first and second conductive layers.

16. (ONCE AMENDED) The semiconductor device according to claim 14, wherein one or more of the wiring patterns of the first conductive layer are electrically connected to one or more of the wiring patterns of the second conductive layer.

17. (ONCE AMENDED) A semiconductor device comprising:

a substrate;

a first set of conductors within a first conductive layer;

a first insulating layer formed over the first set of conductors, the first insulating layer having at least one semiconductor element and the first set of conductors imbedded therein;